

ERRATUM

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# Erratum: Analysis of the physical and photoelectrochemical properties of c-Si(p)/a-SiC:H(p) photocathodes for solar water splitting (2021 *J. Phys. D: Appl. Phys.* **54** 195101)

María del Carmen Mejía<sup>1,\*</sup> , Luis Francisco Sánchez<sup>1</sup>, Mario Kurniawan<sup>2</sup>, Lara Eggert<sup>2</sup>, Alvaro Tejada<sup>3</sup>, Magali Camargo<sup>4</sup> , Rolf Grieseler<sup>1</sup> , Francisco Rumiche<sup>5</sup>, Isabel Díaz<sup>4</sup>, Andreas Bund<sup>2</sup> and Jorge Andrés Guerra<sup>1,\*</sup> 

<sup>1</sup> Departamento de Ciencias, Sección Física, Pontificia Universidad Católica del Perú, Av. Universitaria 1801, 15088 Lima, Perú

<sup>2</sup> Technische Universität Ilmenau, Electrochemistry and Electroplating Group, Gustav-Kirchhoff-Straße 6, 98693 Ilmenau, Germany

<sup>3</sup> Helmholtz-Zentrum Berlin für Materialien und Energie GmbH, Young Investigator Group for Perovskite Tandem Solar Cells, Kekuléstraße 5, 12489 Berlin, Germany

<sup>4</sup> Instituto de Corrosión y Protección, Pontificia Universidad Católica del Perú ICP-PUCP, Av. Universitaria 1801, 15088 Lima, Perú

<sup>5</sup> Departamento de Ingeniería, Sección Ingeniería Mecánica, Pontificia Universidad Católica del Perú, Av. Universitaria 1801, 15088 Lima, Perú

E-mail: [maria.mejia@pucp.edu.pe](mailto:maria.mejia@pucp.edu.pe) and [guerra.jorgea@pucp.edu.pe](mailto:guerra.jorgea@pucp.edu.pe)

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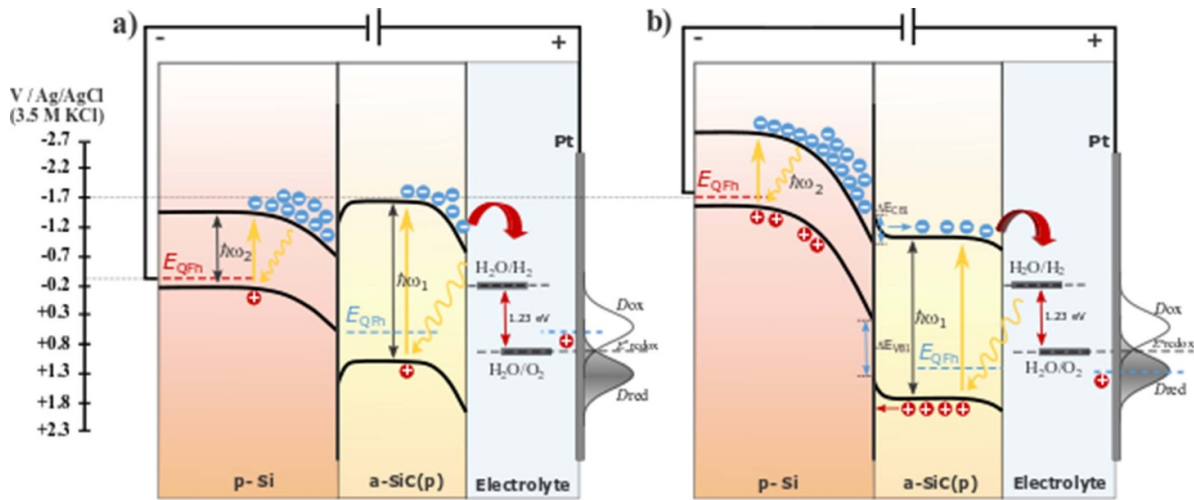
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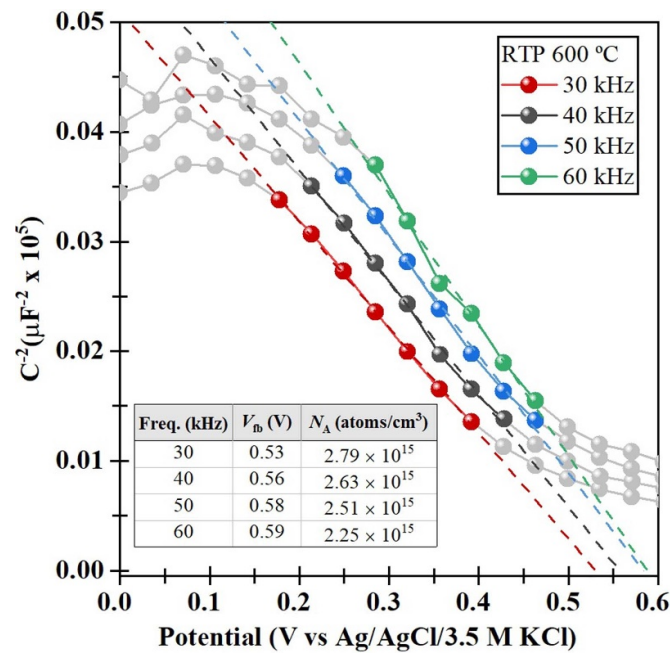
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There was a publishing error regarding the figures of this article. The corrected figures are displayed below.

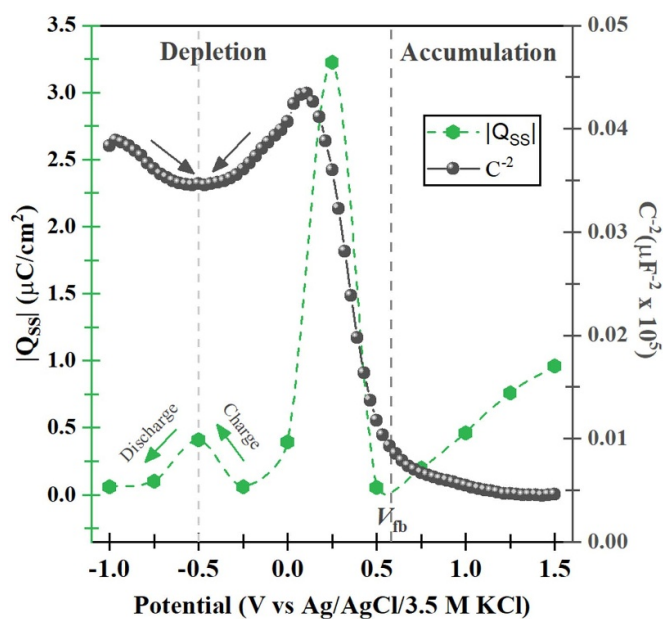
\* Authors to whom any correspondence should be addressed.



**Figure 8.** Energy band diagrams of PEC components: c-Si(p)/a-SiC:H(p) photocathode, anode (Pt) and light illumination, at an applied potential of  $-0.88$  V ( $-0.3$  V vs Ag/AgCl 3.5 M KCl) (a) and under bias at  $-2.85$  V ( $-1.7$  V vs Ag/AgCl 3.5 M KCl) in the ideal band edge pinned situation (b).  $E_{QFh}$  is the quasi-Fermi energy level of holes, represented in each layer.  $E^0_{redox}$  corresponds to the standard redox potential for OER taking place in the Pt counter electrode, whose fluctuation distribution of energy levels are  $D_{red}$  and  $D_{ox}$ .



**Figure 9.** Mott-Schottky plots for the c-Si(p)/a-SiC:H(p) heterojunction annealed at  $600$  °C at frequencies of 30, 40, 50 and 60 kHz. The inset table shows the flat band potential and carrier concentration values obtained from the linear fits performed for each frequency data.




**Figure 14.** Mott–Schottky plot at frequency of 50 kHz and potential-dependent charge in surface states. Surface states charge distributions centered at  $-0.5$  and  $0.25$  V are correlated to the variation in the SCR electronic capacitance behavior observed in the Mott–Schottky plot.

#### ORCID iDs

María del Carmen Mejía  <https://orcid.org/0000-0002-9871-8621>

Magali Camargo  <https://orcid.org/0000-0003-4747-5997>

Rolf Grieseler  <https://orcid.org/0000-0001-5307-7755>

Jorge Andrés Guerra  <https://orcid.org/0000-0002-1734-6660>